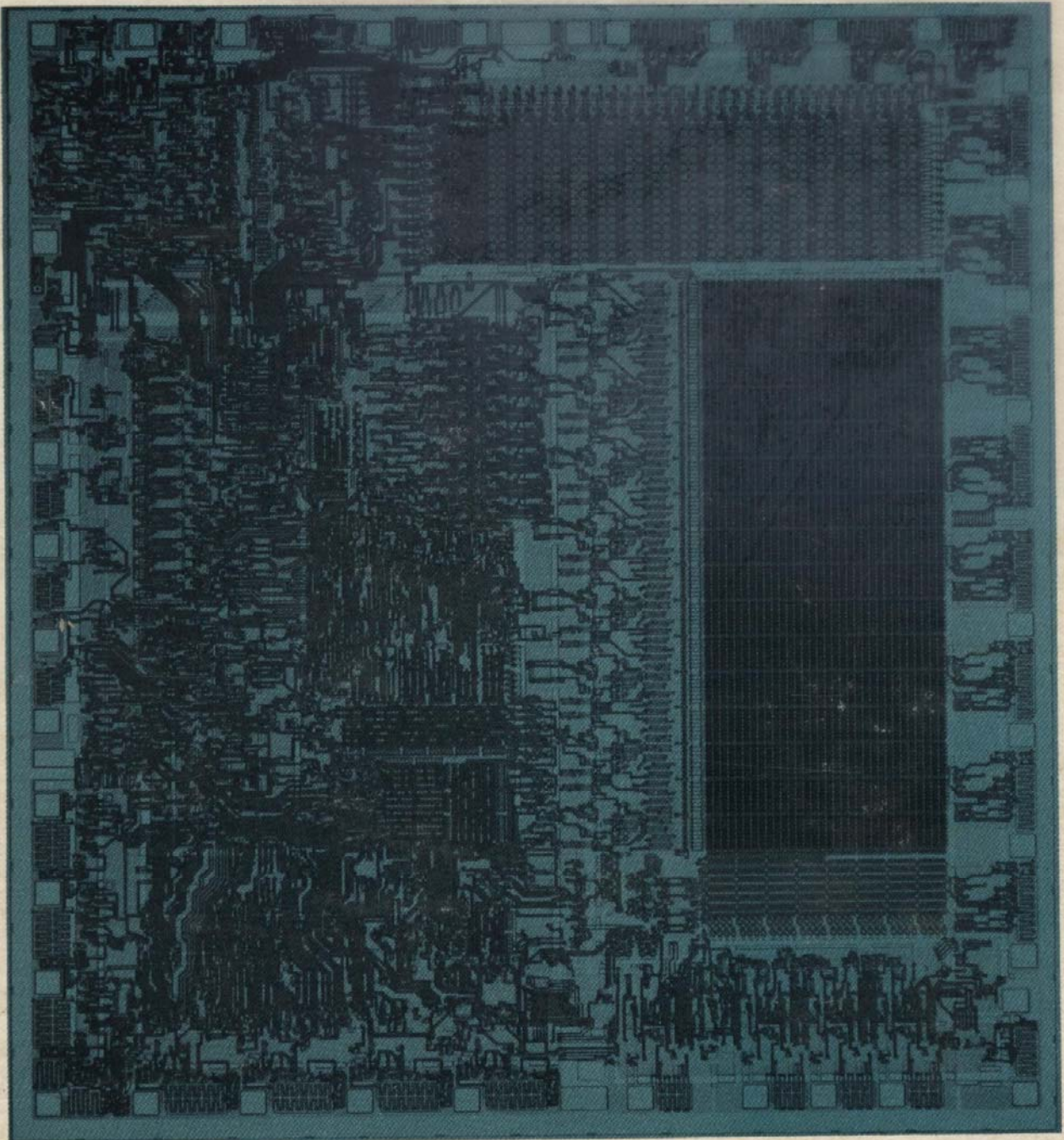


Ben G. Streetman
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ELECTRONIC
DEVICES**
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